



# **isc Silicon PNP Darlingtion Power Transistor**

#### **DESCRIPTION**

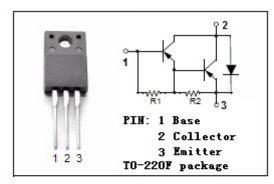
- · High DC Current Gain-
- : h<sub>FE</sub>= 1500(Min.)@I<sub>C</sub>= -3A
- · Low Collector Saturation Voltage-
  - : V<sub>CE(sat)</sub>= -1.5V(Max)@I<sub>C</sub>= -3A
- Good Linearity of h<sub>FE</sub>
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

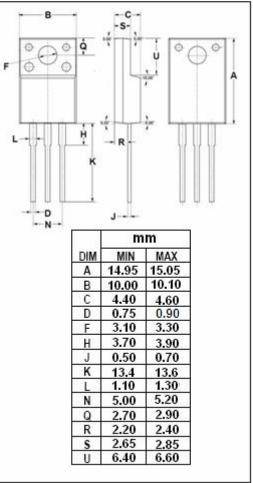
## **APPLICATIONS**

- High power switching applications.
- Hammer drive, pulse motor drive applications.



SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-100	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V	
V <sub>EBO</sub>	Emitter-Base Voltage -7		V	
Ic	Collector Current-Continuous	-7	Α	
Ісм	Collector Current-Peak -10		Α	
I <sub>B</sub>	Base Current-Continuous	-0.5	А	
I <sub>BM</sub>	Base Current-peak	-1	Α	
Pc	Collector Power Dissipation  @ T <sub>C</sub> =25°C	30	W	
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







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2SB1283

### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-100			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -5mA			-1.5	V		
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -5mA			-2.0	V		
І <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-100	μА		
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -100V; R <sub>BE</sub> = ∞			-100	μА		
ІЕВО	Emitter Cutoff Current	V <sub>EB</sub> = -7V; I <sub>C</sub> = 0			-5.0	mA		
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -3V	1500		15000			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.7A; V <sub>CE</sub> = -10V		20		MHz		
Switching Times								
ton	Turn-on Time				1.0	μ <b>S</b>		
t <sub>stg</sub>	Storage Time	$I_{C}$ = -3.0A , $I_{B1}$ = - $I_{B2}$ = -5mA, $V_{CC}$ $\approx$ -40V; $R_{L}$ = 10 $\Omega$			4.0	μ <b>S</b>		
t <sub>f</sub>	Fall Time				2.0	μ \$		

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